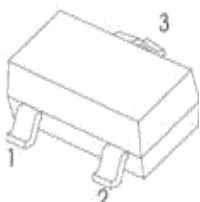
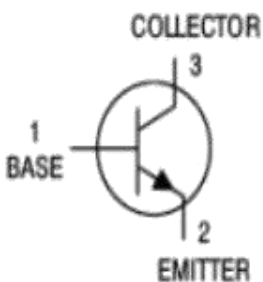


TRANSISTOR (NPN)		SOT-23 Plastic-Encapsulate Transistors	
<p style="text-align: center;"><u>SOT-23</u></p>   <p>1 .BASE 2.EMITTER 3.COLLECTOR</p> <p style="text-align: center;">Marking :J6</p>		<p style="text-align: center;">Features</p> <p>※ Complimentary to S9015</p> <p>※ Collector Current: Ic=0.5A</p>	
MAXIMUM RATINGS (Ta=25°C unless otherwise noted)			
Parameter	Symbol	Value	Unit
Collector-Base Voltage	VCBO	50	V
Collector-Emitter Voltage	VCEO	45	V
Emitter-Base Voltage	VEBO	6	V
Collector Current	IC	100	mA
Collector Power Dissipation	PC	450	mW
Thermal Resistance From Junction To Ambient	RθJA	625	°C/W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55~+150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC= 100μA, IE=0	50	145	200	V
Collector-emitter breakdown voltage	V(BR)CEO	IC= 1mA, IB=0	45	78	100	V
Emitter-base breakdown voltage	V(BR)EBO	IE= 100μA, IC=0	6	10.5	30	V
Collector cut-off current	ICBO	VCB= 50 V , IE=0			0.1	μ A
Collector cut-off current	ICEO	VCB= 35V , IE=0			1	μ A
Emitter cut-off current	IEBO	VEB= 6V , IC=0			0.1	μ A
DC current gain	hFE	VCE=5V, IC= 1mA	300		450	
	hFE	VCE=5V, IC= 10mA	150			
Collector-emitter saturation voltage	VCE(sat)	IC=100 mA, IB= 10mA			0.3	V
Base-emitter saturation voltage	VBE(sat)	IC=100 mA, IB= 10mA			1.3	V
Transition frequency	fT	VCE=6V, IC= 20mA f=30MHz	150			MHz
CLASSIFICATION OF hFE						
HEF	300-400					
MARKING	J6					

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

